Supporting Information: Physical Vapor Deposition Features of Ultrathin Nanocrystals of $Bi_2(Te_xSe_{1-x})_3$

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Supporting Information Available



Supplementary Figure 1: SEM image of a sample for thickness measurement. The top and bottom surface of TI are indicated with the upper and lower white lines, respectively.



Supplementary Figure 2: The dependence of Unit cell volume on the substitution ratio of Se atoms obtained from Vegard's law. The solid line represent the lattice parameters calculated from Vegard's law.¹



Supplementary Figure 3: Typical Energy Dispersive X-RAY spectroscopy of $Bi_2(Te_{1-x}Se_x)_3$ nanoplate.



Supplementary Figure 4: Electron backscatter diffraction. a: SEM image (obtained with the EBSD system) of $Bi_2(Te_{1-x}Se_x)_3$ nanoplate on Si substrate located outside of Nbelectrodes b-d: EBSD crystallographic orientation mappings of $Bi_2(Te_{1-x}Se_x)_3$ using nverse pole figure (IPF-X, IPF-Y, and IPF-Z), respectively. e: Color code for the mappings in (bd). f-h: EBSD crystallographic orientation mappings of Si substrate using IPF-X, IPF-Y, and IPF-Z, respectively. (i) Color code for the mappings in (f-h). j: EBSD inverse pole figure (IPF) of the $Bi_2(Te_{1-x}Se_x)_3$ nanoplate along X, Y, and Z directions, respectively. r: EBSD inverse pole figure (IPF) of the Si subsrate along X, Y, and Z directions, respectively

References

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 3161.



Supplementary Figure 5: Independent 4-point ${\rm R}({\rm T})$ measurements of our 140nm thick Nb film.



Supplementary Figure 6: SEM images of samples S7 and S8.